

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)	Atty. Docket No. 070050.2717	Serial No. 10/525,297
	Applicant James S. Im	
	Filing Date 2/15/2005	Group <del>2811</del> 2822
	Examiner Bac H. Au	

### FOREIGN PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Applicant(s)
/BA/	1.	WO 0197266	12/20/2001	Mitsubishi Denki Kabushiki Kaisha
/BA/	2.	WO 0171791	09/27/2001	The Trustees of Columbia University In The City of New York

NY02:587010.1			
Examiner	/Bac Au/	Date Considered	07/31/2007

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10/525297  
PCI/PTO 15 FEB 2005

PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

**(Use as many sheets as necessary)**

Sheet	1	of	1
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**Complete if Known**

Application Number	<del>Not yet assigned</del> 10/525297
Filing Date	<del>Herewith</del> 2/15/2005
First Named Inventor	James S. Im
Art Unit	<del>Not yet assigned</del> 2822
Examiner Name	<del>Not yet assigned</del> Bac H. Au
Attorney Docket Number	A35413-PCT-USA (070050.2717)

## U. S. PATENT DOCUMENTS

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	2	4234358	11/18/1980	Celler et al.
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↓	129	6563077	05/13/2003	Im

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
/BA/	154	Im <i>et al.</i> , "On the Super Lateral Growth Phenomenon Observed in Excimer Laser-Induced Crystallization of Thin Si Films," Appl. Phys. Lett., Vol. 64 (17), p. 2303 (1994).
	155	Brochure from MicroLas Lasersystem, GmbH, "UV Optics Systems for Excimer Laser Based Micromaching and Marking". 1999.
	156	Ishida et al., "Ultra-shallow boxlike profiles fabricated by pulsed ultraviolet-laser doping process", J. Vac. Sci. Technol. B 12(1), p. 399-403, 1994. (No month).
	157	Yoshimoto, et al., "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, AM-LCD 2000. No month.
	158	Ozawa et al., "Two-Dimensionally Position-Controlled Exicem-Laser-Crystallization of Silicon Thin Films on Glassy Substrate", Jpn. J. Appl. Phys. vol. 38, Part 1, No. 10, p. 5700-5705, (1999). No month.
	159	I.W. Boyd, Laser Processing of Thin Films and Microstructures, Oxidation, Deposition, and Etching of Insulators (Springer--Verlag Berlin Heidelber 1987).*
	160	N. Yamamuchi and R. Reif, Journal of Applied Physics, "Polycrystalline silicon thin films processed with silicon ion implantation and subsequent solid-phase crystallization: Theory, experiments, and thin-film transistor applications" -- April 1, 1994 -- Volume 75, Issue 7, pp. 3235-3257
	161	T. Noguchi, "Appearance of Single-Crystalline Properties in Fine-Patterned Si Thin Film Transistors (TFTs) by Solid Phase Crystallization (SPC)," Jpn. J. Appl. Phys. Vol. 32 (1993) L1584-L1587
	162	Ishihara et al., "A Novel Double-Pulse Exicem-Laser Crystallization Method of Silicon Thin-Films," Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 34, no. 8A, August 1995, pp. 3976-3981
✓	163	Kim, H. J., "Excimer-Laser-Induced Crystallization of Amorphous Silicon Thin Films", Ph. D. Dissertation Abstract, Columbia University, 1996.*

NY02:531132.1

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/Bac Au/

Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.